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[SEM-98] Nanoelectric and photovoltaic caracterization of CuInSe2 films doped with active metals

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Investigation has been made as to the incorporation of electrically beneficial for CuInSe2 impurities, such as with sodium doping. It has been found that the grain boundaries of the CIS not create deep levels and therefore are neutral. However, they have not tested other active dopants that could improve the performance observed with sodium. In this work they were electrodeposited CuInSe2 the films on copper substrates using a bathroom with Cu ratios: Se: In 1: 1: 2. To increase crystallinity and reducer the presence of phases undesirable as Cu-Se or Se films electrochemical post-treatment were carried to the films applying a negative potential in the presence of Se4+ and subsequently a potential positive in the same solution[1]. The films were doped with four electrochemically active metals at three different levels of doping, applying an additional negative potential during deposition. The films were characterized by Raman spectroscopy, atomic force microscopy with current measurement (CAFM), IV macro with light without light and photoelectrochemical current. IV curves and electrical CAFM images by finding an improved rectifying behavior of current with decreasing charge density of the dopant and local variations in conductivity of the materials are compared. The effect of doping on the microstructure and photocurrent measurements and electrochemical photocurrent described. [1] F. Caballero-Briones, L.E. Arvizu-Rodríguez, A. Palacios-Padrós, S. Jiménez-Sandoval, F. Chalé-Lara, J.L. Fernández-Muñoz, I. Díez-Pérez, F. Sanz, F.J Espinosa-Faller, Phase and surface modification by electrochemical post deposition treatments in ultrasonic-assisted CuInSe2/Cu electrodeposited films properties. Sent: Chalcogenide Letters.